

RT1P14HX SERIES

〈Transistor〉

Transistor With Resistor
For Switching Application
Silicon PNP Epitaxial Type

DESCRIPTION

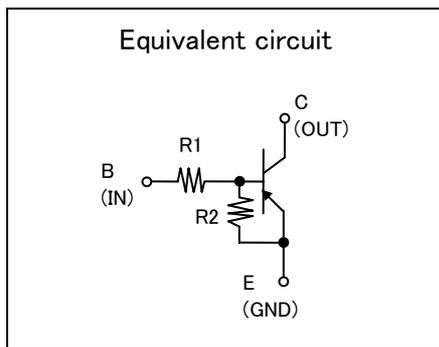
RT1P14HX is a one chip transistor with built-in bias resistor, NPN type is RT1N14HX.

FEATURE

• Built-in bias resistor (R1=10kΩ, R2=4.7kΩ).

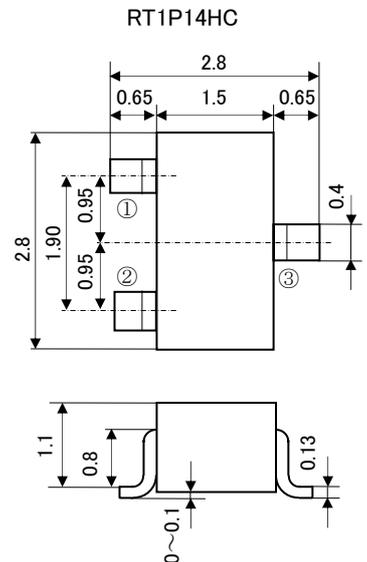
APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit.



OUTLINE DRAWING

UNIT : mm

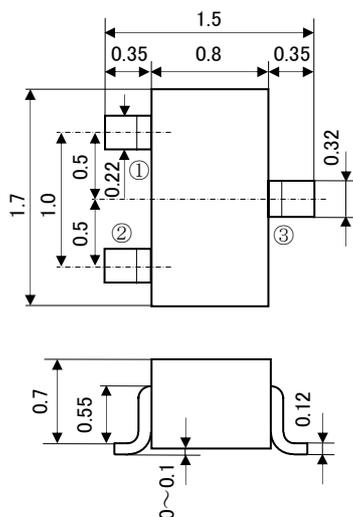


JEITA: SC-59
JEDEC: Similar to TO-236

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P14HU

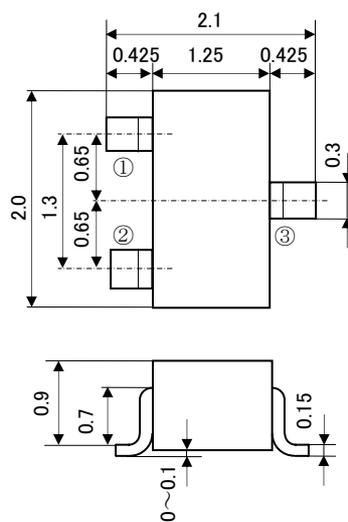


JEITA: SC-75A
JEDEC: —

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P14HM

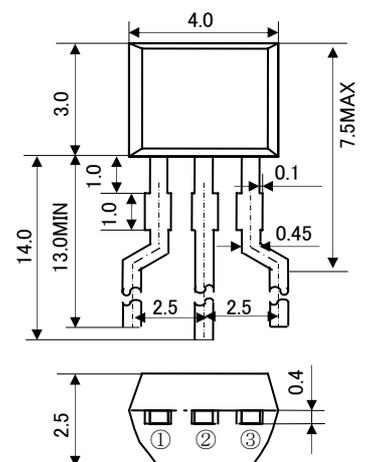


JEITA: SC-70
JEDEC: —

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P14HS



JEITA: —
JEDEC: —

Terminal Connector

- ①: Emitter
- ②: Collector
- ③: Base

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MARKING

RT1P14HC RT1P14HM RT1P14HU	RT1P14HS

MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING				UNIT
		RT1P14HU	RT1P14HM	RT1P14HC	RT1P14HS	
V _{CBO}	Collector to Base voltage	-50				V
V _{EBO}	Emitter to Base voltage	-10				V
V _{CEO}	Collector to Emitter voltage	-50				V
V _{IN}	Input voltage	-30				V
I _C	Collector current	-100				mA
I _{CM}	Peak Collector current	-200				mA
P _C	Collector dissipation(Ta=25°C)	150	200	450	mW	
T _j	Junction temperature	+150				°C
T _{stg}	Storage temperature	-55~+150				°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

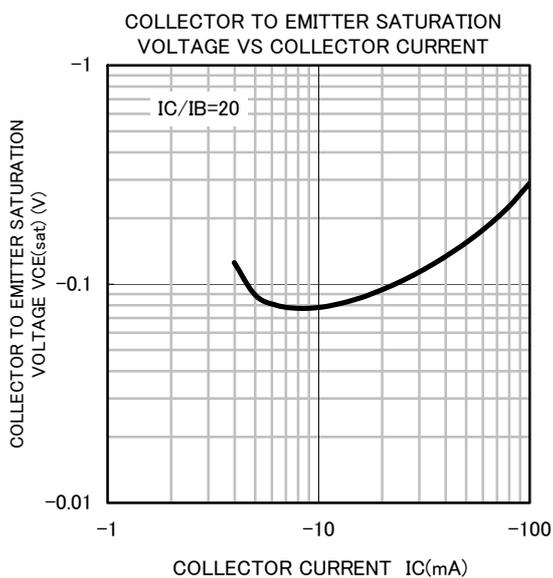
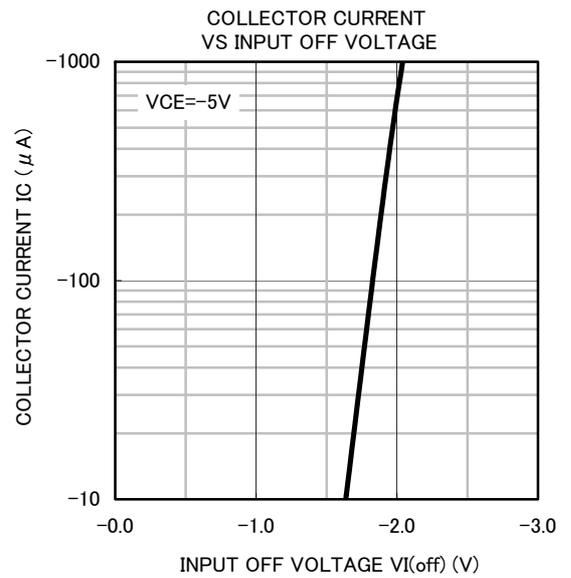
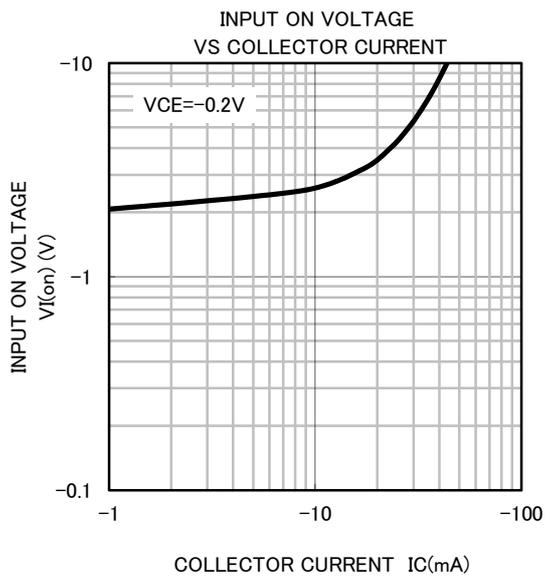
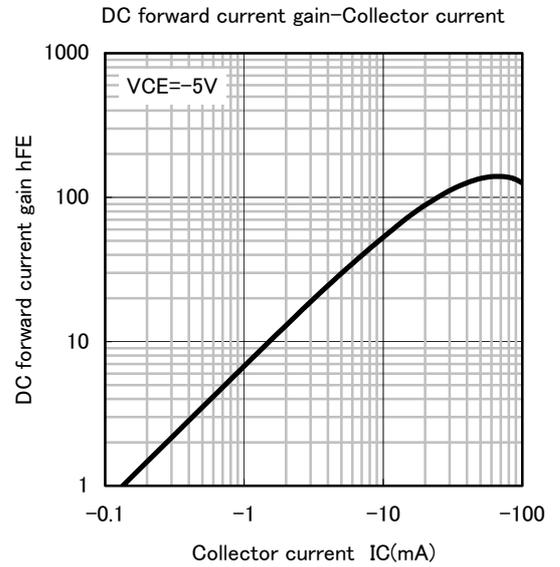
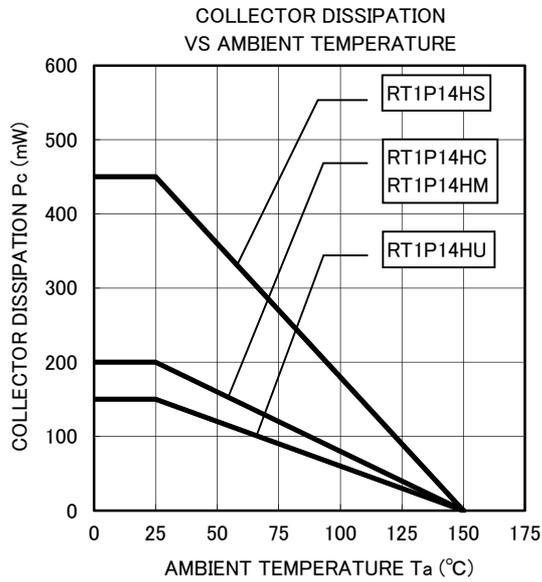
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V _{(BR)CEO}	C to E break down voltage	I _C = -100 μA, R _{BE} = ∞	-50	—	—	V
I _{CBO}	Collector cut off current	V _{CB} = -50V, I _E = 0	—	—	-0.1	μA
I _{EBO}	Emitter cut off current	V _{EB} = -5V, I _C = 0	-255	-340	-493	μA
h _{FE}	DC forward current gain	V _{CE} = -5V, I _C = -10mA	24	—	—	—
V _{CE(sat)}	C to E saturation voltage	I _C = -10mA, I _B = -0.5mA	—	—	-0.3	V
V _{I(ON)}	Input on voltage	V _{CE} = -0.2V, I _C = -5mA	—	-2.1	-3.8	V
V _{I(OFF)}	Input off voltage	V _{CE} = -5V, I _C = -100 μA	-1.3	-1.7	—	V
R ₁	Input resistor	—	7	10	13	kΩ
R ₂ /R ₁	Resistor ratio	—	0.37	0.47	0.57	—
f _T	Gain band width product	V _{CE} = -6V, I _E = 10mA	—	150	—	MHz

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TYPICAL CHARACTERISTICS (Ta=25°C)





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